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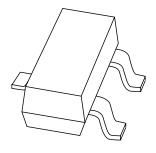
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BF570NPN medium frequency transistor

Product data sheet Supersedes data of 2004 Jan 13 2004 Mar 15



NXP Semiconductors Product data sheet

NPN medium frequency transistor

BF570

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 15 V)
- Low feedback capacitance (max. 2.2 pF).

APPLICATIONS

- Monitors
- Battery equipped applications.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

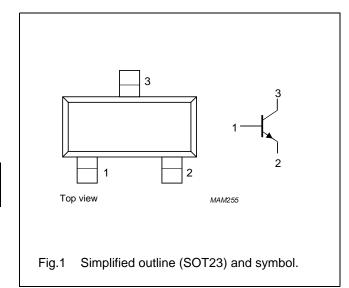
TYPE NUMBER	MARKING CODE(1)
BF570	61* or B26

Note

1. * = p : Made in Hong Kong.* = t : Made in Malaysia.* = W : Made in China.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



ORDERING INFORMATION

TYPE		PACKAGE	
NUMBER	NAME	DESCRIPTION	VERSION
BF570	_	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	15	V
I _{CM}	peak collector current		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	-	250	mW
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 1 V	40	_	
f _T	transition frequency	I _C = 40 mA; V _{CE} = 10 V; f = 100 MHz	490	_	MHz

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NXP Semiconductors Product data sheet

NPN medium frequency transistor

BF570

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	40	V
V _{CEO}	collector-emitter voltage	open base	_	15	V
V _{EBO}	emitter-base voltage	open collector	-	4.5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	500	K/W

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0 A; V _{CB} = 20 V	_	_	400	nA
		$I_E = 0 \text{ A}; V_{CB} = 20 \text{ V}; T_j = 125 ^{\circ}\text{C}$	_	_	30	μΑ
I _{EBO}	emitter cut-off current	I _C = 0 A; V _{EB} = 2 V	_	_	100	nA
h _{FE}	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V}$	40	_	_	
C _{re}	feedback capacitance	I _C = 0 A; V _{CE} = 10 V; f = 1 MHz	_	1.6	2.2	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	500	_	_	MHz
		$I_C = 40 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	490	_	_	MHz

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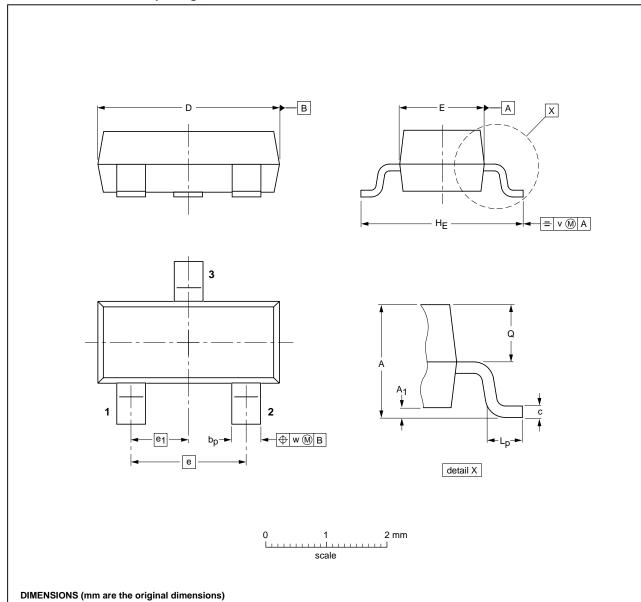
NPN medium frequency transistor

BF570

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE		REFER	RENCES	EUROPEAN ISSUE D	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT23		TO-236AB			04-11-04

 $L_{\mathbf{p}}$

0.45

Q

0.1

 $\mathbf{H}_{\mathbf{E}}$

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 A_1

max.

bp

0.38

UNIT

NXP Semiconductors Product data sheet

NPN medium frequency transistor

BF570

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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